256K (32K x 8)

5-Volt Only

CMOS Flash

PEROM

Features

- Fast Read Access Time 90 ns
- Five-Volt-Only Reprogramming
- **Page Program Operation**

Single Cycle Reprogram (Erase and Program) Internal Address and Data Latches for 64 Bytes

- Internal Program Control and Timer
- Hardware and Software Data Protection
- **Fast Program Cycle Times**
 - Page (64 Byte) Program Time 10 ms Chip Erase Time - 10 ms
- **DATA Polling for End of Program Detection**
- Low Power Dissipation

50 mA Active Current

300 µA CMOS Standby Current

- Typical Endurance > 10,000 Cycles
- Single 5 V ± 10% Supply
- CMOS and TTL Compatible Inputs and Outputs
- Commercial and Industrial Temperature Ranges

Description

The AT29C256 is a five-volt-only in-system Flash programmable and erasable read only memory (PEROM). Its 256K of memory is organized as 32,768 words by 8 bits. Manufactured with Atmel's advanced nonvolatile CMOS technology, the device offers access times to 90 ns with power dissipation of just 275 mW. When the device is deselected, the CMOS standby current is less than 300 µA. The device endurance is such that any sector can typically be written to in excess of 10,000 times. (continued)

Pin Configurations

Function
Addresses
Chip Enable
Output Enable
Write Enable
Data Inputs/Outputs
No Connect

DIP Top View

			1	
WE [1	28	Ь	Vcc
A12 🗆	2	27		A14
A7 A6	2 3 4 5 6 7	26	þ	A13
A6 🗆	4	25	Ь	A8
A5 C	5	24	Þ	A9
A4 🗆	6	23	b	A11
A3 🗆	7	22	ь	ÕĒ
A2 🗆	8	21	Ь	A10
A2 [9	20	Ь	CE
A0 🗆	10	19	Ь	1/Q7
VO0 🗆	11	18	Ь	1/06
I/01 🗆	12	17	Ь	1/05
1/02	13	16	Ь	1/04
GND 🗆	14	15	þ	1/03
			1	

PLCC and LCC Top View



TSOP Top View

Type 1

OE	A11	a a	23	22	21	20	'n	CE	A10
A9	A8		25	24	19	20 18	Ĕ	VO6	1/07
A13	Δ14	9	27	26	17	16	É	1/04	1/05
vcc	WE	₽	1	28	15	14	6	GND	I/O3 I/O2
A12	A7	3	3	2	13	12	B	VO1	
A6	A5	3	5	4	11	10	B	A0	1/00
A4	АЗ	4_	7	6	9	8	Б	A2	A1

Note: PLCC package pins 1 and are DON'ECONNECT.



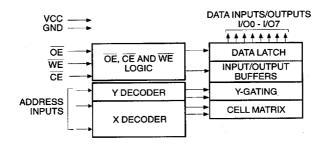


Description (Continued)

To allow for simple in-system reprogrammability, the AT29C256 does not require high input voltages for programming. Five-volt-only commands determine the operation of the device. Reading data out of the device is similar to reading from a static RAM. Reprogramming the AT29C256 is performed on a page basis; 64 bytes of data are loaded into the device and then simultaneously programmed. The contents of the entire device may be erased by using a six-byte software code (although erasure before programming is not needed).

During a reprogram cycle, the address locations and 64 bytes of data are internally latched, freeing the address and data bus for other operations. Following the initiation of a program cycle, the device will automatically erase the page and then program the latched data using an internal control timer. The end of a program cycle can be detected by DATA polling of I/O7. Once the end of a program cycle has been detected a new access for a read, program or chip erase can begin.

Block Diagram



Device Operation

READ: The AT29C256 is accessed like a static RAM. When TE and OE are low and WE is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in the high impedance state whenever $\overline{\text{CE}}$ or $\overline{\text{OE}}$ is high. This dual-line control gives designers flexibility in preventing bus contention.

BYTE LOAD: A byte load is performed by applying a low pulse on the \overline{WE} or \overline{CE} input with \overline{CE} or \overline{WE} low (respectively) and OE high. The address is latched on the falling edge of CE or WE, whichever occurs last. The data is latched by the first rising edge of \overline{CE} or \overline{WE} . Byte loads are used to enter the 64 bytes of a page to be programmed or the software codes for data protection and chip erasure.

PROGRAM: The device is reprogrammed on a page basis. If a byte of data within a page is to be changed, data for the entire page must be loaded into the device. Any byte that is not loaded during the programming of its page will be erased to read FFh. Once the bytes of a page are loaded into the device, they are simultaneously programmed during the internal programming period. After the first data byte has been loaded into the device, successive bytes are entered in the same manner. Each new byte to be programmed must have its high to low transition on WE (or CE) within 150 µs of the low to high transition of WE (or CE) of the preceding byte. If a high to low transition is not detected within 150 µs of the last low to high transition, the load period will end and the internal programming period will start. A6 to A14 specify the page address. The page address must be valid during each high to low transition of WE (or CE). A0 to A5 specify the byte address within the page. The bytes may be loaded in any order; sequential loading is not required. Once a programming operation has been initiated, and for the duration of twc, a read operation will effectively be a polling operation. SOFTWARE DATA PROTECTION: A software controlled data protection feature is available on the AT29C256. Once the software protection is enabled a software algorithm must be issued to the device before a program may be performed. The software protection feature may be enabled or disabled by the user; when shipped from Atmel, the software data protection feature is disabled. To enable the software data protection, a series of three program commands to specific addresses with specific data must be performed. After the software data protection is enabled the same three program commands must begin each program cycle in order for the programs to occur. All software program commands must obey the page program timing specifications. Once set, the software data protection feature remains active unless its disable command is issued. Power transitions will not reset the software data protection feature, however the software feature will guard against inadvertent program cycles during power transitions.

Once set, software data protection will remain active unless the disable command sequence is issued.

After setting SDP, any attempt to write to the device without the three-byte command sequence will start the internal write timers. No data will be written to the device; however, for the duration of twc, a read operation will effectively be a polling

After the software data protection's three-byte command code is given, a byte load is performed by applying a low pulse on the \overline{WE} or \overline{CE} input with \overline{CE} or \overline{WE} low (respectively) and \overline{OE} high.

(continued)





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Device Operation (Continued)

The address is latched on the falling edge of \overline{CE} or \overline{WE} , whichever occurs last. The data is latched by the first rising edge of \overline{CE} or \overline{WE} . The 64 bytes of data must be loaded into each sector by the same procedure as outlined in the program section under device operation.

HARDWARE DATA PROTECTION: Hardware features protect against inadvertent programs to the AT29C256 in the following ways: (a) V_{CC} sense— if V_{CC} is below 3.8 V (typical), the program function is inhibited. (b) V_{CC} power on delay— once V_{CC} has reached the V_{CC} sense level, the device will automatically time out 5 ms (typical) before programming. (c) Program inhibit— holding any one of \overline{OE} low, \overline{CE} high or \overline{WE} high inhibits program cycles. (d) Noise filter— pulses of less than 15 ns (typical) on the \overline{WE} or \overline{CE} inputs will not initiate a program cycle.

PRODUCT IDENTIFICATION: The product identification mode identifies the device and manufacturer and may be accessed by a hardware operation. For details, see Operating Modes or Product Identification.

DATA POLLING: The AT29C256 features DATA polling to indicate the end of a program cycle. During a program cycle an attempted read of the last byte loaded will result in the complement of the loaded data on I/O7. Once the program cycle has been completed, true data is valid on all outputs and the next cycle may begin. DATA polling may begin at any time during the program cycle.

TOGGLE BIT: In addition to DATA polling the AT29C256 provides another method for determining the end of a program or erase cycle. During a program or erase operation, successive attempts to read data from the device will result in I/O6 toggling between one and zero. Once the program cycle has completed, I/O6 will stop toggling and valid data will be read. Examining the toggle bit may begin at any time during a program cycle.

OPTIONAL CHIP ERASE MODE: The entire device can be

erased by using a six-byte software code. Please see Software

Chip Erase application note for details.

Absolute Maximum Ratings*

Temperature Under Bias55°C to +125°C
Storage Temperature65°C to +150°C
All Input Voltages (including N.C. Pins) with Respect to Ground0.6 V to +6.25 V
All Output Voltages with Respect to Ground0.6 V to V _{CC} +0.6 V
Voltage on $\overline{\text{OE}}$ with Respect to Ground0.6 V to +13.5 V

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Pin Capacitance $(f = 1 \text{ MHz}, T = 25^{\circ}\text{C})^{(1)}$

	Тур	Max	Units	Conditions
Cin	4	6	pF	V _{IN} = 0 V
Соит	8	12	pF	Vout = 0 V

Note: 1. This parameter is characterized and is not 100% tested.





D.C. and A.C. Operating Range

		AT29C256-90	AT29C256-12	AT29C256-15	AT29C256-20	AT29C256-25
Operating	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C∙- 70°C
Temperature (Case)		-40°C - 85°C				
Vcc Power Supply		5 V± 10%	5 V± 10%	5 V± 10%	5 V ± 10%	5 V ± 10%

Operating Modes

Mode	CE	ŌĒ	WE	Ai	1/0
Read	VIL	VIL	ViH	Ai	Douт
Program ⁽²⁾	VIL	ViH	VIL	Ai	DIN
5V Chip Erase	VIL	ViH	VIL	Ai	
Standby/Write Inhibit	ViH	X ⁽¹⁾	Х	X	High Z
Write Inhibit	Х	X	ViH		
Write Inhibit	Х	VIL	Х		
Output Disable	Х	ViH	Χ		High Z
High Voltage Chip Erase	VIL	V _H ⁽³⁾	VIL	X	High Z
Product Identification				A1-A14 = V _{IL} , A9 = V _H , A0 = V _{IL}	Manufacturer Code ⁽⁴⁾
Hardware	VIL	VIL	ViH	A1-A14 = V _{IL} , A9 = V _H , A0 = V _{IH}	Device Code ⁽⁴⁾
(E)				A0 = V _{IL}	Manufacturer Code ⁽⁴⁾
Software ⁽⁵⁾				A0 = ViH	Device Code ⁽⁴⁾

Notes: 1. X can be V_{IL} or V_{IH} .

2. Refer to A.C. Programming Waveforms.

3. $V_H = 12.0 \text{ V} \pm 0.5 \text{ V}$.

4. Manufacturer Code: 1F, Device Code: DC

5. See details under Software Product Identification Entry/Exit.

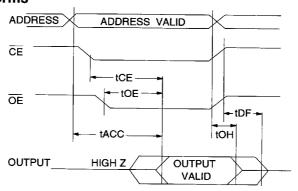
D.C. Characteristics

Symbol	Parameter	Condition	Min	Max	Units
lu	Input Load Current	V _{IN} = 0 V to V _{CC}		10	μΑ
ILO	Output Leakage Current	V _{I/O} = 0 V to V _{CC}		10	μΑ
I _{SB1}	V _{CC} Standby Current CMOS	CE = Vcc-0.3 V to Vcc		300	μΑ
ISB2	Vcc Standby Current TTL	CE = 2.0 V to Vcc		3	mA
lcc	V _{CC} Active Current	f = 5 MHz; lout = 0 mA		50	mA
VIL	Input Low Voltage			0.8	V
VIH	Input High Voltage		2.0		V
Vol	Output Low Voltage	loL = 2.1 mA		.45	V
VOL VOH1	Output High Voltage	I _{OH} = -400 μA	2.4		٧
VOH1 VOH2	Output High Voltage CMOS	I _{OH} = -100 μA; V _{CC} = 4.5 V	4.2		V

A.C. Read Characteristics

			C256- 90		C256- 12	1	C256- 15	1	C256- 20	ŀ	C256- 25	
Symbol	Parameter	Min	Max	Units								
tacc	Address to Output Delay		90		120		150		200		250	ns
tce (1)	CE to Output Delay		90		120		150		200		250	ns
toe (2)	OE to Output Delay	0	40	0	50	0	70	0	80	0	100	ns
t _{DF} (3,4)	CE or OE to Output Float	0	25	0	30	0	40	0	50	0	60	ns
tон	Output Hold from OE, CE or Address, whichever occurred first	0		0		0		0		0		ns

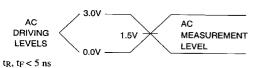
A.C. Read Waveforms^(1,2,3,4)



Notes:

- CE may be delayed up to tACC tCE after the address transition without impact on tACC.
- DE may be délayed up to t_{CE} t_{OE} after the falling edge of CE without impact on t_{CE} or by t_{ACC} t_{OE} after an address change without impact on t_{ACC}.
- 3. t_{DF} is specified from \overline{OE} or \overline{CE} whichever occurs first $(C_L = 5pF)$.
- 4. This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



Output Test Load



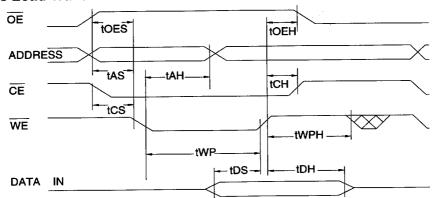




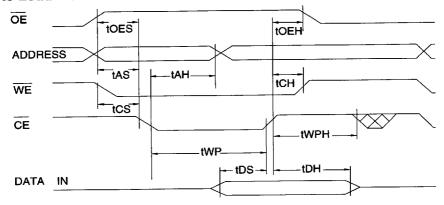
A.C. Byte Load Characteristics

	B	Min	Max	Units
Symbol	Parameter	141111	INUX	
tas, toes	Address, OE Set-up Time	00		ns
t _{AH}	Address Hold Time	50		ns
tcs	Chip Select Set-up Time	0		ns
tсн	Chip Select Hold Time	0		ns
twp	Write Pulse Width (WE or CE)	90		ns
tos	Data Set-up Time	50		ns
tDH,tOEH	Data, OE Hold Time	0		ns
twph	Write Pulse Width High	100		ns

A.C. Byte Load Waveforms- WE Controlled



A.C. Byte Load Waveforms- $\overline{\text{CE}}$ Controlled

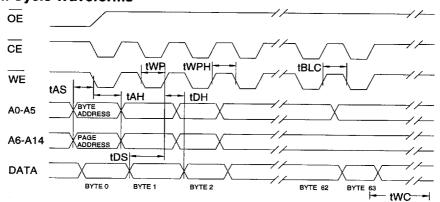


AT29C256

Program Cycle Characteristics

Symbol	Parameter	Min	Max	Units
twc	Write Cycle Time		10	ms
tas	Address Set-up Time	0		ns
tah	Address Hold Time	50		ns
tos	Data Set-up Time	50		ns
tDH	Data Hold Time	0		ns
twp	Write Pulse Width	90		ns
tBLC	Byte Load Cycle Time		150	μs
twpH	Write Pulse Width High	100		ns

Program Cycle Waveforms(1,2,3)



Notes: 1. A6 through A14 must specify the page address during each high to low transition of WE (or CE).
2. OE must be high when WE and CE are both low.

as paragram

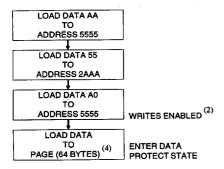
10-

3. All bytes that are not loaded within the page being programmed will be erased to FF.





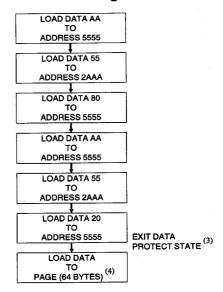
Software Data Protection Enable Algorithm (1)



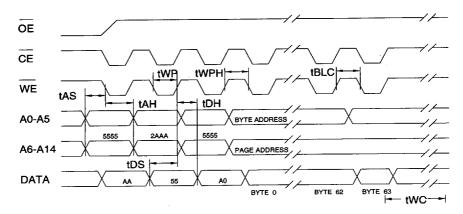
Notes for software program code:

- 1. Data Format: I/O7 I/O0 (Hex); Address Format: A14 - A0 (Hex).
- 2. Data Protect state will be activated at end of program cycle.
- 3. Data Protect state will be deactivated at end of program period.
- 4. 64 bytes of data must be loaded.

Software Data Protection Disable Algorithm (1)



Software Protected Program Cycle Waveform (1,2,3)



Notes: 1. A6 through A14 must specify the page address during each high to low transition of $\overline{\text{WE}}$ (or $\overline{\text{CE}}$) after the software code has been entered.

- 2. \overline{OE} must be high when \overline{WE} and \overline{CE} are both low.
- 3. All bytes that are not loaded within the page being programmed will be erased to FF.

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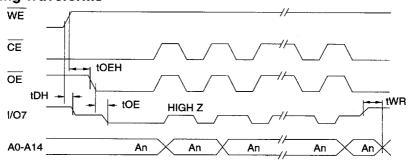
AT29C256

Data Polling Characteristics(1)

Symbol	Parameter	Min	Тур	Max	Units
tон	Data Hold Time	0			ns
toeh	OE Hold Time	10			ns
toE	OE to Output Delay ⁽²⁾				ns
twR	Write Recovery Time	0			ns

- Notes: 1. These parameters are characterized and not 100% tested.
 - 2. See toE spec in A.C. Read Characteristics.

Data Polling Waveforms

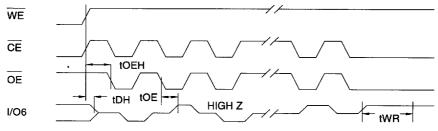


Toggle Bit Characteristics(1)

Symbol	Parameter	Min	Тур	Max	Units
toh	Data Hold Time	0	. =		ns
toeh	OE Hold Time	10	382.		ns
toE	OE to Output Delay ⁽²⁾				ns
toehp	OE High Pulse	150			ns
twn	Write Recovery Time	0			ns

- Notes: 1. These parameters are characterized and not 100% tested.
 - See toE spec in A.C. Read Characteristics.

Toggle Bit Waveforms (1,2,3)



Notes:

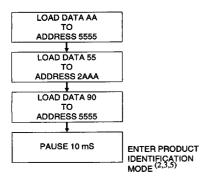
- 1. Toggling either \overline{OE} or \overline{CE} or both \overline{OE} and \overline{CE} will operate toggle bit.
- 2. Beginning and ending state of I/O6 will vary.
- 3. Any address location may be used but the address should not vary.



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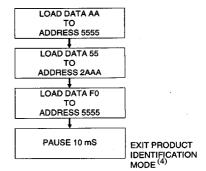
Software Product Identification Entry (1)



Notes for software product identification:

- Data Format: I/O7 I/O0 (Hex);
 Address Format: A14 A0 (Hex).
- A1 A14 = V_{IL}.
 Manufacture Code is read for A0 = V_{IL};
 Device Code is read for A0 = V_{IH}.
- The device does not remain in identification mode if powered down.
- 4. The device returns to standard operation mode.
- Manufacturer Code: 1F Device Code: DC

Software Product (1) Identification Exit

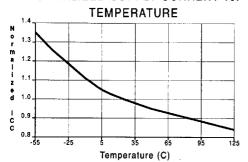




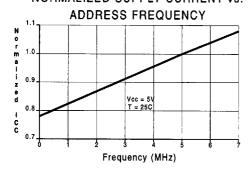




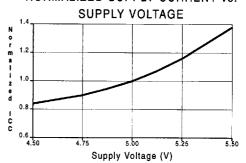
NORMALIZED SUPPLY CURRENT vs.



NORMALIZED SUPPLY CURRENT vs.



NORMALIZED SUPPLY CURRENT vs.



3



Ordering Information

tacc	Icc (mA)		Ordering Code	Package	Operation Range
(ns)	Active	Standby	Ordering Code	Раскаде	Operation hange
90	50	0.3	AT29C256-90DC AT29C256-90JC AT29C256-90PC	28D6 32J 28P6	Commercial (0° to 70°C)
90	50	0.3	AT29C256-90TC	28T	Commercial (0° to 70°C)
			AT29C256-90JI AT29C256-90TI	32J 28T	Industrial (-40° to 85°C)
120	50	0.3	AT29C256-12DC AT29C256-12JC AT29C256-12LC AT29C256-12PC AT29C256-12TC	28D6 32J 32L 28P6 28T	Commercial (0° to 70°C)
			AT29C256-12DI AT29C256-12JI AT29C256-12LI AT29C256-12PI	28D6 32J 32L 28P6	Industrial (-40° to 85°C)
150	50	0.3	AT29C256-15DC AT29C256-15JC AT29C256-15LC	28D6 32J 32L	Commercial (0° to 70°C)
			AT29C256-15DI AT29C256-15JI AT29C256-15LI AT29C256-15PI AT29C256-15TI	28D6 32J 32L 28P6 28T	Industrial (-40° to 85°C)
200	50	0.3	AT29C256-20DC AT29C256-20JC AT29C256-20LC AT29C256-20PC	28D6 32J 32L 28P6	Commercial (0° to 70°C)
			AT29C256-20DI AT29C256-20JI AT29C256-20LI AT29C256-20PI	28D6 32J 32L 28P6	Industrial (-40° to 85°C)
250	50	0.3	AT29C256-25DC AT29C256-25JC AT29C256-25LC AT29C256-25PC	28D6 32J 32L 28P6	Commercial (0° to 70°C)
250	50	0.3	AT29C256-25DI AT29C256-25JI AT29C256-25LI AT29C256-25PI	28D6 32J 32L 28P6	Industrial (-40° to 85°C)

Package Type					
28D6	28 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual Inline Package (Cerdip)				
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)				
32L	32 Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)				
28P6	28 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)				
28T	28 Lead, Thin Small Outline Package (TSOP)				